



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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TECHNOLOGY CENTER 2800

In re Application of

Sawazaki, et al.

Serial No.: 09/522,832

Group Art Unit: 2815

Filed: March 10, 2000

Examiner: Baumeister, B.

For: GROUP III NITRIDE COMPOUND SEMICONDUCTOR LIGHT-EMITTING  
DEVICE

#25/D  
Amdt.  
J. McInulla  
2/3/03

Honorable Assistant Commissioner of Patents  
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to evaluation on the merits, please amend the above-identified Application as follows:

IN THE CLAIMS:

Please revise the claims to read as follows.

SUB  
E17

D1

1. (Three Times Amended) A group III nitride compound semiconductor light-emitting device, comprising:
- a light-emitting layer of a multilayer quantum well structure composed of alternately laminated well layers and barrier layers; and
  - an n-type clad layer being in contact with said light-emitting layer, wherein said n-type clad layer is made thicker than each of said barrier layers and the thickness of said n-type clad layer is in a range of 100 Å to 500 Å, and
  - wherein said n-type clad layer is formed of a material substantially the same as said barrier layers, thereby providing a band gap in said n-type clad layer that is substantially the same as a band gap in said barrier layers.

Please add the following new claims: